

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
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Attorney D ck t No. 0756-1961

Serial No. N t Y t Assign d

INFORMATION DISCLOSURE STATEMENT

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Applicant: Shunpei YAMAZAKI t al.

Filing Date:

Group: 2812

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
Loke	4,727,044	2/23/88	Yamazaki			
Loke	4,959,700	9/25/90	Yamazaki			
Loke	5,142,344	5/24/91	Yamazaki			
Loke	4,415,383	11/15/83	Naem et al.			
Loke	4,523,962	6/18/85	Nishimura			
Loke	4,431,459	2/14/84	Teng			
Loke	4,851,363	7/25/89	Troxel et al.			
Loke	4,959,700	9/25/90	Yamazaki			2/3/88
Loke	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91
Loke	4,561,906	12/31/85	Calder et al.	437	101	10/24/83
Loke	5,091,334	2/25/92	Yamazaki et al.	437	101	6/29/81
Loke	5,272,361	12/21/93	Yamazaki	257	66	6/13/90

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation Yes No
Loke	59-121876	7/14/84	Japan			Abstract
Loke	60-245174	12/4/85	Japan			Abstract
Loke	6-59280	3/4/94	Japan			Abstract
Loke	5-206468	8/13/93	Japan			Abstract
Loke	1-187983	7/27/89	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Loke		Sameshima et al., Japanese Journal of Applied Physics, "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Vol. 28, No. 10, October, 1989, p. 1789-1793.
Loke		Sera et al., "High Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous Silicon Film", IEEE Transactions, 36 (1989), p. 2868-2872.

Examiner

Loke

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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
Loke	5,077,235	12/31/91	Kosaka	437	72	1/16/90
Loke	5,306,651	4/26/94	Masumo et al.	437	40	5/10/91
Loke	4,814,292	3/21/89	Sasaki et al.	437	101	6/19/87
Loke	5,298,434	3/29/94	Strater et al.	437	21	2/7/92
Loke	5,313,076	5/17/94	Yamazaki et al.	257	66	3/17/92
Loke	4,727,044	2/23/88	Yamazaki	437	45	

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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	0 023 429	5/82	Japan	437	978		
	0 178 447	4/86	Japan	437	173		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Loke		Kiang et al., "Modification of S/C Device Chas. by Lasers", IBM, 1982, p. 171-6.
Loke		Sameshima et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", Mat. Res Soc. Symp Proc. Vol. 71, 1986, p. 435-440.
Loke		Iwamatsu et al., "Silicon on Sapphire MOSFETs Fabricated by Back Surface Laser Anneal Technology", Electronics Letters, Vol. 15, No. 25, p. 827-828, December, 1979.

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